

| L Number | Hits | Search Text  | DB  | Time stamp       |
|----------|------|--|---|------------------|
| 1        | 248  | (dopant impurity) near3 (layer film) same (anodic anode anodization) near10 (oxid\$5)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/08 07:04 |
| 2        | 21   | ((dopant impurity) near3 (layer film) same (anodic anode anodization) near10 (oxid\$5)) and (separat\$3 cleav\$3 break\$3) near5 substrate                     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/08 07:06 |
| 3        | 14   | ((((dopant impurity) near3 (layer film) same (anodic anode anodization) near10 (oxid\$5)) and (separat\$3 cleav\$3 break\$3) near5 substrate) and @ad<19981222 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/08 07:06 |